

# SIHF510-VB Datasheet N-Channel 100-V (D-S) MOSFET

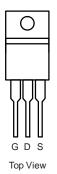
PRODUCT	SUMMARY		
V <sub>(BR)DSS</sub> (V)	$R_{DS(on)}(\Omega)$	I <sub>D</sub> (A)	
100	0.127at V <sub>GS</sub> = 10 V	18	

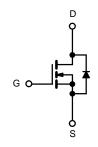
#### **FEATURES**

- Trench Power MOSFET
- 175 °C Junction Temperature
- Low Thermal Resistance Package
- 100 % R<sub>g</sub> Tested



## TO-220AB





N-Channel MOSFET

## APPLICATIONS

• Isolated DC/DC Converters

ABSOLUTE MAXIMUM RATINGS T <sub>C</sub> = 25 °C, unless otherwise noted							
Parameter	Symbol	Limit	Unit				
Drain-Source Voltage	V <sub>DS</sub>	100	V				
Gate-Source Voltage	V <sub>GS</sub>	± 20	1 V				
Continuous Drain Current (T <sub>.1</sub> = 175 °C)	T <sub>C</sub> = 25 °C	L	18				
Continuous Diain Current (1j = 175 C)	T <sub>C</sub> = 125 °C	I <sub>D</sub>	15	A			
Pulsed Drain Current		I <sub>DM</sub>	68				
Avalanche Current	L = 0.1 mH	I <sub>AS</sub>	18				
Single Pulse Avalanche Energy <sup>b</sup>	L = 0.1 mm	E <sub>AS</sub>	200	mJ			
Mariana Barra Biada atia h	T <sub>C</sub> = 25 °C	В	105	W			
Maximum Power Dissipation <sup>b</sup>	T <sub>A</sub> = 25 °C <sup>d</sup>	P <sub>D</sub>	3.75	vv			
Operating Junction and Storage Temperature Ra	inge	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 175	°C			

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Limit	Unit		
Junction-to-Ambient	PCB Mount (TO-263) <sup>d</sup>	$R_{thJA}$	40	°C/W		
Junction-to-Case (Drain)		R <sub>thJC</sub>	0.4	C/VV		

#### Notes:

- a. Package limited.
- b. Duty cycle  $\leq$  1 %.
- c. See SOA curve for voltage derating.
- d. When Mounted on 1" square PCB (FR-4 material).



Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	$V_{DS} = 0 \text{ V}, I_{D} = 250 \mu\text{A}$	100			V	
Gate-Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2		4	V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
		V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 0 V			1		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C			50	μΑ	
		V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 175 °C			250		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	120			Α	
		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 20 A		0.127			
Drain-Source On-State Resistance <sup>a</sup>	r <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 20 A, T <sub>J</sub> = 125 °C		0.130		Ω	
		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 20 A, T <sub>J</sub> = 175 °C		0.170			
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 20 A	25			S	
Dynamic <sup>b</sup>							
Input Capacitance	C <sub>iss</sub>			1300		pF	
Output Capacitance	C <sub>oss</sub>	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 25 V, f = 1 MHz		260			
Reverse Transfer Capacitance	C <sub>rss</sub>			110			
Total Gate Charge <sup>c</sup>	Qg				28		
Gate-Source Charge <sup>c</sup>	$Q_{gs}$	$V_{DS} = 100 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 65 \text{ A}$			4.8	nC	
Gate-Drain Charge <sup>c</sup>	$Q_{gd}$				15		
Gate Resistance	R <sub>g</sub>		0.5	1.7	3.3	Ω	
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			8			
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD} = 100 \text{ V}, R_{L} = 1.5 \Omega$		120		ns	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>	$I_D \cong 65 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 2.5 \Omega$		25			
Fall Time <sup>c</sup>	t <sub>f</sub>			50		1	
Source-Drain Diode Ratings and Cha	aracteristics 7	T <sub>C</sub> = 25 °C <sup>b</sup>					
Continuous Current	I <sub>S</sub>			18		۸	
Pulsed Current	I <sub>SM</sub>			68		Α	
Forward Voltage <sup>a</sup>	V <sub>SD</sub>	I <sub>F</sub> = 65 A, V <sub>GS</sub> = 0 V		1.0	1.5	V	
Reverse Recovery Time	t <sub>rr</sub>			130	200	ns	
Peak Reverse Recovery Current	I <sub>RM(REC)</sub>	I <sub>F</sub> = 50 A, di/dt = 100 A/μs		8	12	Α	
Reverse Recovery Charge	Q <sub>rr</sub>			0.52	1.2	μC	

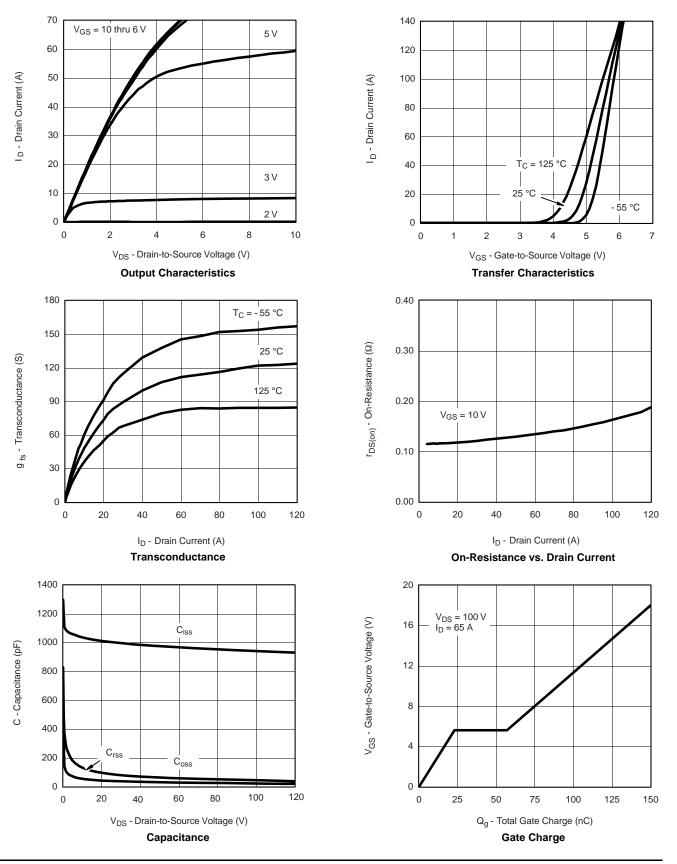
#### Notes:

- a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

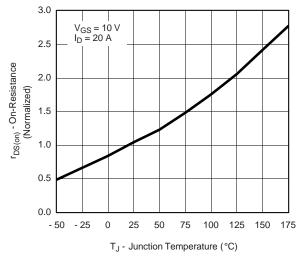


## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

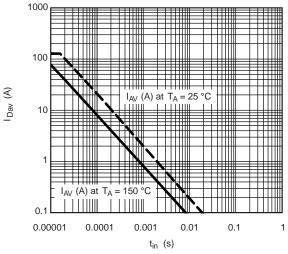




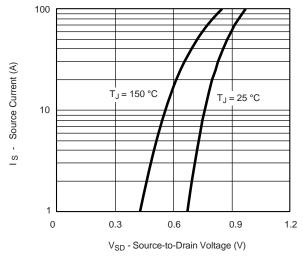
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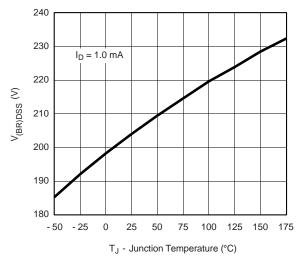
On-Resistance vs. Junction Temperature



**Avalanche Current vs. Time** 



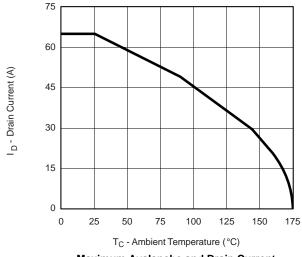
Source-Drain Diode Forward Voltage



Drain Source Breakdown vs. Junction Temperature



#### THERMAL RATINGS



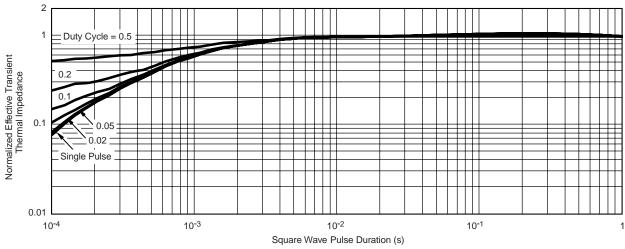
r<sub>DS(on)</sub> Limited

1000

Maximum Avalanche and Drain Current vs. Case Temperature

\*  $V_{GS}$  > minimum  $V_{GS}$  at which  $r_{DS(on)}$  is specified

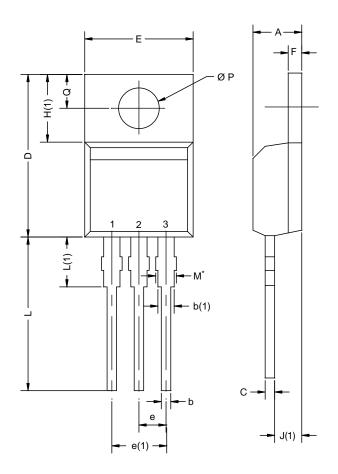
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case



# **TO-220AB**



	MILLIN	IETERS	INC	HES		
DIM.	MIN.	MAX.	MIN.	MAX.		
А	4.25	4.65	0.167	0.183		
b	0.69	1.01	0.027	0.040		
b(1)	1.20	1.73	0.047	0.068		
С	0.36	0.61	0.014	0.024		
D	14.85	15.49	0.585	0.610		
Е	10.04	10.51	0.395	0.414		
е	2.41	2.67	0.095	0.105		
e(1)	4.88	5.28	0.192	0.208		
F	1.14	1.40	0.045	0.055		
H(1)	6.09	6.48	0.240	0.255		
J(1)	2.41	2.92	0.095	0.115		
L	13.35	14.02	0.526	0.552		
L(1)	3.32	3.82	0.131	0.150		
ØΡ	3.54	3.94	0.139	0.155		
Q	2.60	3.00	0.102	0.118		
ECN: X12-0208-Rev. N, 08-Oct-12 DWG: 5471						

#### Notes

 $<sup>^{\</sup>star}$  M = 1.32 mm to 1.62 mm (dimension including protrusion) Heatsink hole for HVM



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